freescale
飞思卡尔(深圳)功率半导体有限公司

AO5600E

Complementary Enhancement Mode Field Effect Transistor

General Description

The AO5600E/L uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications.AO5600E and AO5600EL are electrically identical.

-RoHS compliant

-AO5600EL is Halogen Free

Features

n-channel

V_{DS} (V) = 20V, I_D = 0.6A (V_{GS}=4.5V)

$R_{DS(ON)}$< 0.65Ω (V_{GS}= 4.5V)

$R_{DS(ON)}$< 0.75Ω (V_{GS}= 2.5V)

$R_{DS(ON)}$< 0.95Ω (V_{GS}= 1.8V)

p-channel

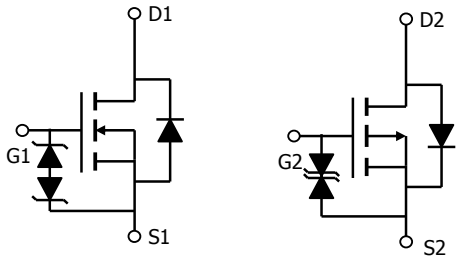
V_{DS} (V) = -20V, I_D = -0.5A (V_{GS}=-4.5V)

$R_{DS(ON)}$< 0.8Ω (V_{GS}= -4.5V)

$R_{DS(ON)}$< 1.0Ω (V_{GS}= -2.5V)

$R_{DS(ON)}$< 1.3Ω (V_{GS}= -1.8V)

RoHS Compliant



Absolute Maximum Ratings T_A=25°C unless otherwise noted					
Parameter		**Symbol**	**Max n-channel**	**Max p-channel**	**Units**
Drain-Source Voltage		V_{DS}	20	-20	V
Gate-Source Voltage		V_{GS}	±8		V
Continuous Drain Current [B,H]	T_C=25°C	I_D	0.6	-0.5	A
	T_C=100°C		0.4	-0.38	
Pulsed Drain Current [B]		I_{DM}	3	-1	
Power Dissipation	T_C=25°C	P_D	0.38	0.38	W
	T_C=100°C		0.24	0.24	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics: n-channel and p-channel						
Parameter		**Symbol**	**Device**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	n-ch	275	330	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		n-ch	360	450	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	n-ch	300	350	°C/W
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	p-ch	275	330	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		p-ch	360	450	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	p-ch	300	350	°C/W

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N-channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±4.5V			±1	µA
		V_{DS}=0V, V_{GS}=±8V			±100	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	0.45	0.6	1	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	3			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=0.5A		0.54	0.65	Ω
		T_J=125°C		0.81	1	
		V_{GS}=2.5V, I_D=0.5A		0.63	0.75	Ω
		V_{GS}=1.8V, I_D=0.3A		0.73	0.95	Ω
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=0.5A		1.5		S
V_{SD}	Diode Forward Voltage	I_S=0.1A,V_{GS}=0V		0.65	1	V
I_S	Maximum Body-Diode Continuous Current				0.4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz		35	45	pF
C_{oss}	Output Capacitance			8		pF
C_{rss}	Reverse Transfer Capacitance			6		pF
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=0.5A		0.63	1	nC
Q_{gs}	Gate Source Charge			0.08		nC
Q_{gd}	Gate Drain Charge			0.16		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=5V, V_{DS}=10V, R_L=50Ω, R_{GEN}=3Ω		4.5		ns
t_r	Turn-On Rise Time			3.3		ns
$t_{D(off)}$	Turn-Off DelayTime			70		ns
t_f	Turn-Off Fall Time			35		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=0.5A, dI/dt=100A/µs		8	10	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=0.5A, dI/dt=100A/µs		2		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using <300 µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

F. The maximum current rating is limited by bond-wires

Rev5: Oct 2008

N-Channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

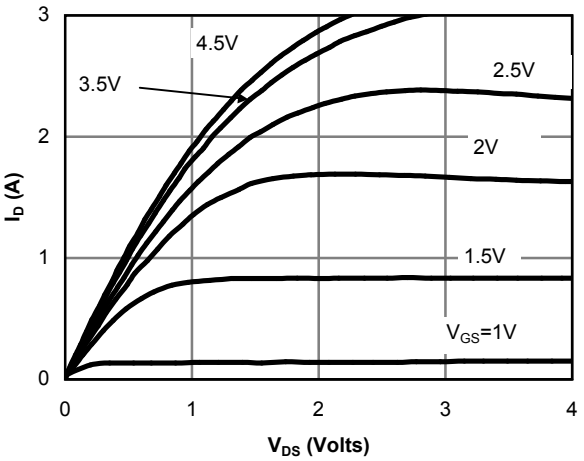

Figure 1: On-Region Characteristics

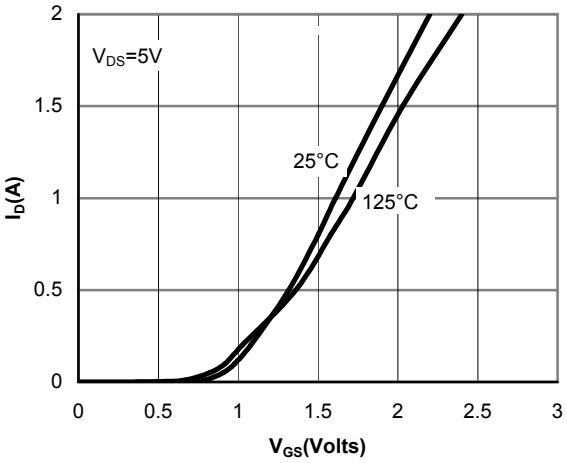

Figure 2: Transfer Characteristics

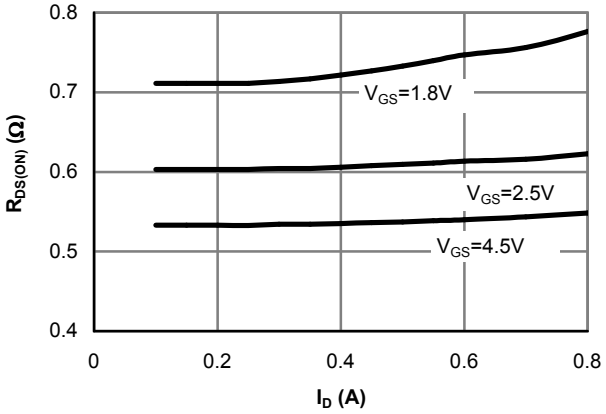

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

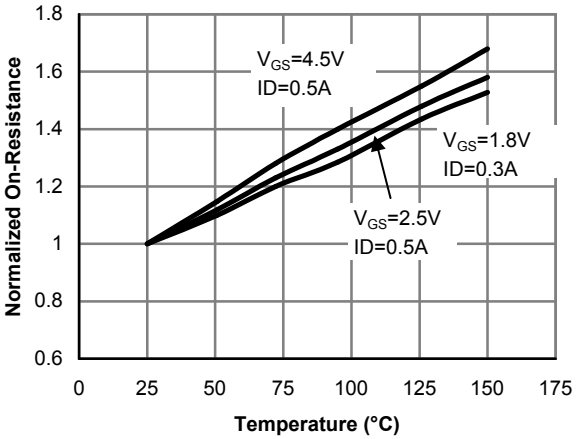

Figure 4: On-Resistance vs. Junction Temperature

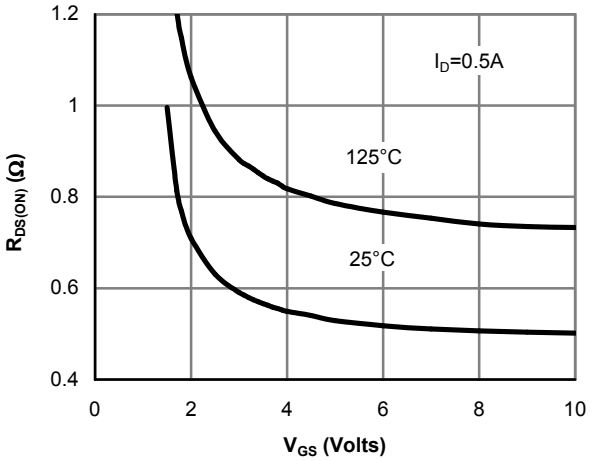

Figure 5: On-Resistance vs. Gate-Source Voltage

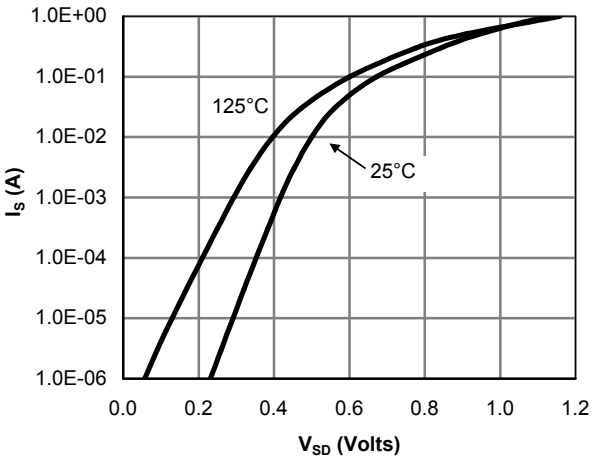

Figure 6: Body-Diode Characteristics

N-Channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

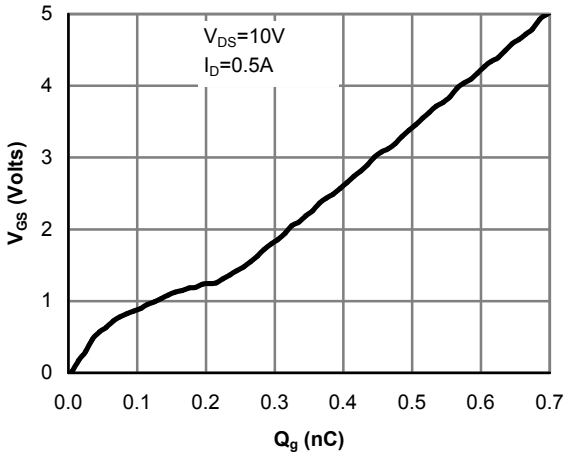

Figure 7: Gate-Charge Characteristics

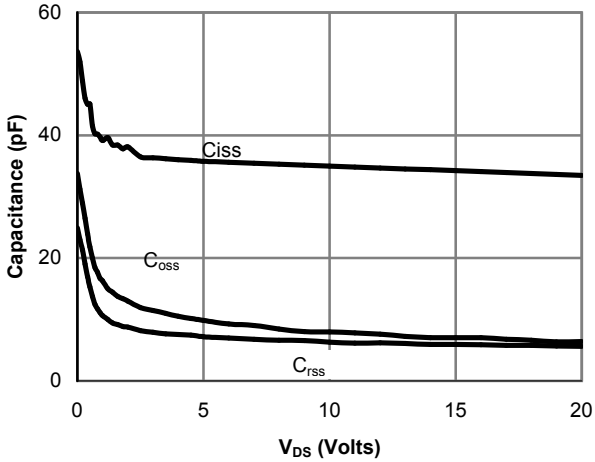

Figure 8: Capacitance Characteristics

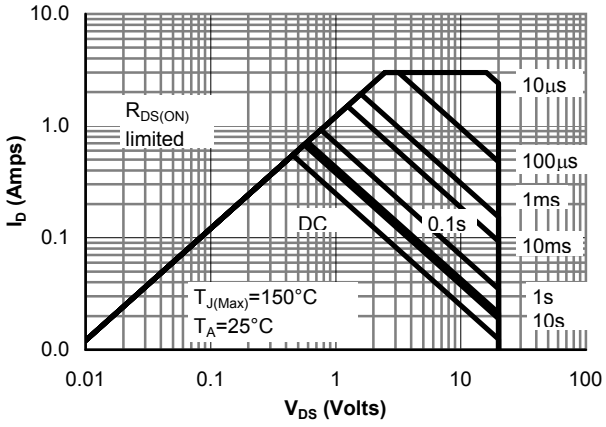

Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

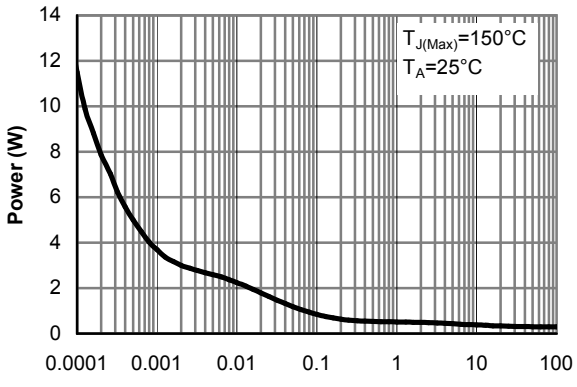

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

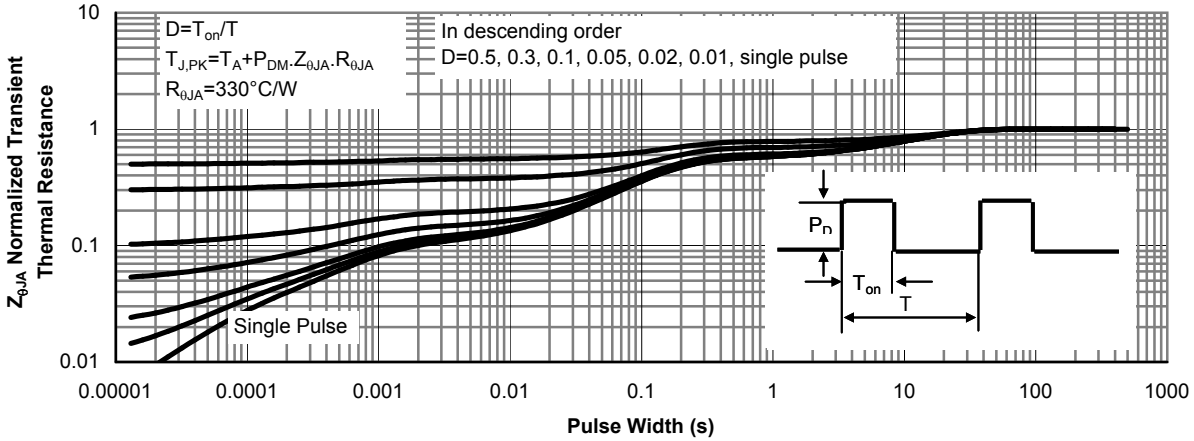

Figure 11: Normalized Maximum Transient Thermal Impedance

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Complementary Enhancement Mode Field Effect Transistor

P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±4.5V			±1	µA
		V_{DS}=0V, V_{GS}=±8V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-1	-0.6	-0.45	
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-1			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-0.5A		0.65	0.8	Ω
		T_J=125°C		0.9	1.1	
		V_{GS}=-2.5V, I_D=-0.5A		0.85	1	Ω
		V_{GS}=-1.8V, I_D=-0.3A		1.05	1.3	Ω
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-0.51A		0.9		S
V_{SD}	Diode Forward Voltage	I_S=-0.1A,V_{GS}=0V		-0.66	-1	V
I_S	Maximum Body-Diode Continuous Current				-0.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		72	100	pF
C_{oss}	Output Capacitance			17		pF
C_{rss}	Reverse Transfer Capacitance			9		pF
SWITCHING PARAMETERS						
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=50Ω, R_{GEN}=3Ω		60.5		ns
t_r	Turn-On Rise Time			150		ns
$t_{D(off)}$	Turn-Off DelayTime			612		ns
t_f	Turn-Off Fall Time			436		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-0.5A, dI/dt=100A/µs		27	35	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-0.5A, dI/dt=100A/µs		8.3		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6,12,14 are obtained using <300 µs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.
F. The maximum current rating is limited by bond-wires
Rev5: Oct 2008

P-Channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

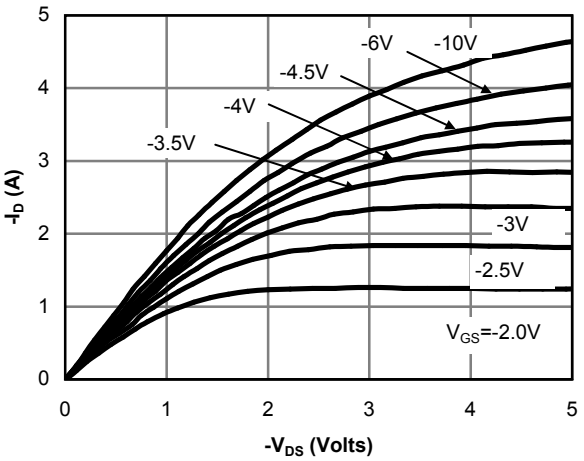


Figure 1: On-Region Characteristics

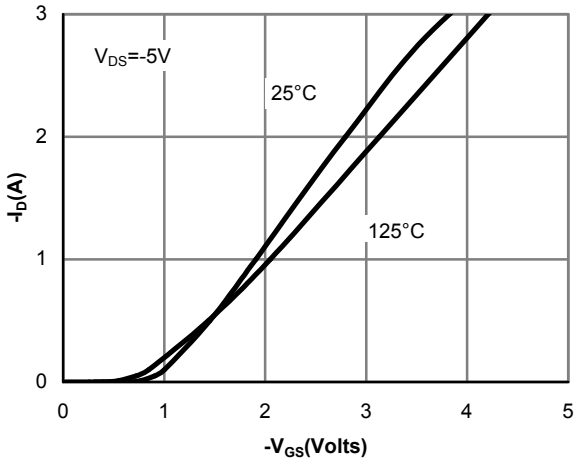


Figure 2: Transfer Characteristics

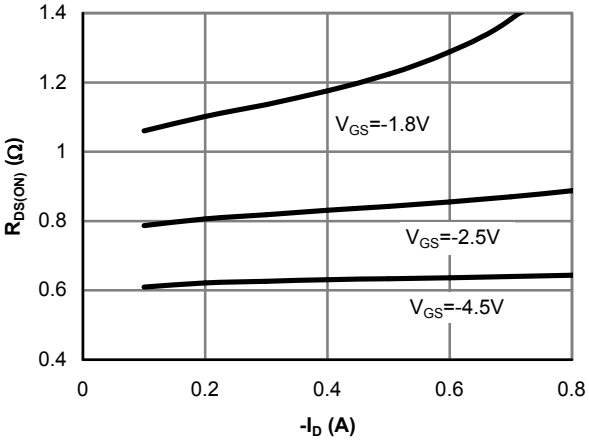


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

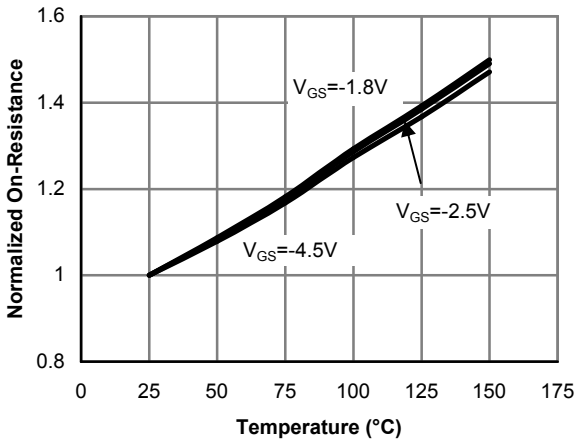


Figure 4: On-Resistance vs. Junction Temperature

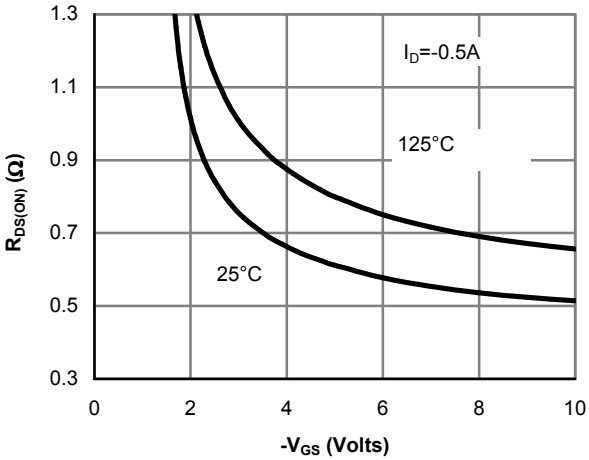


Figure 5: On-Resistance vs. Gate-Source Voltage

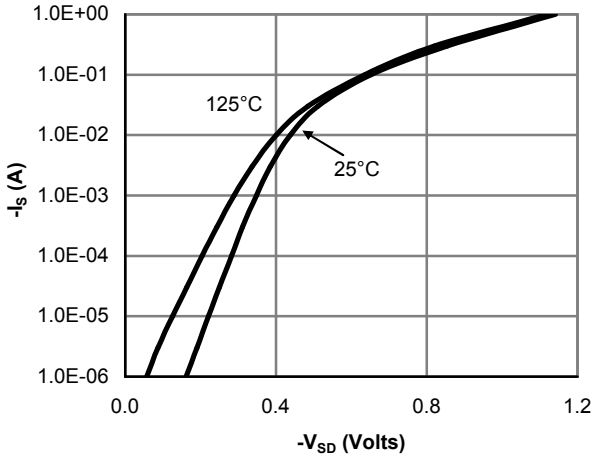


Figure 6: Body-Diode Characteristics

P-Channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

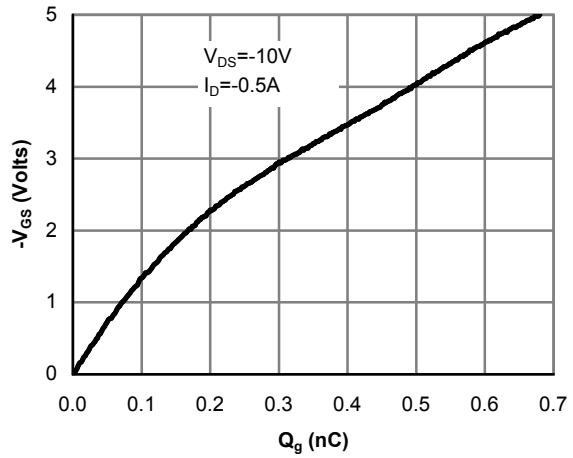


Figure 7: Gate-Charge Characteristics

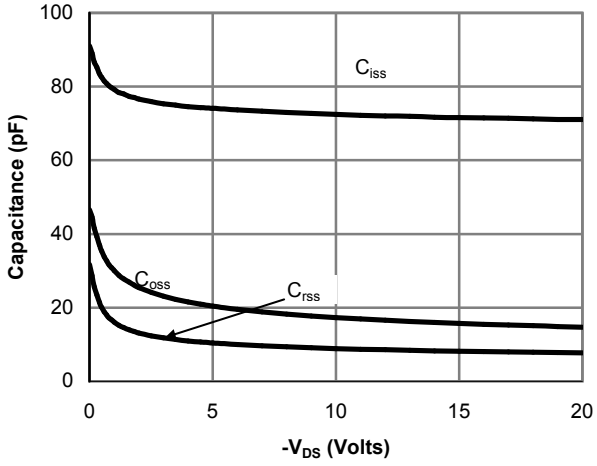


Figure 8: Capacitance Characteristics

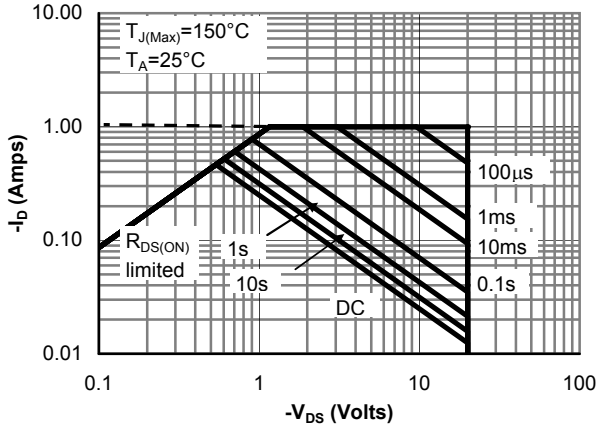


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

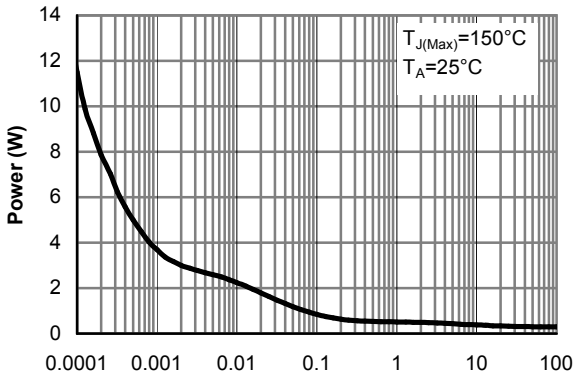


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

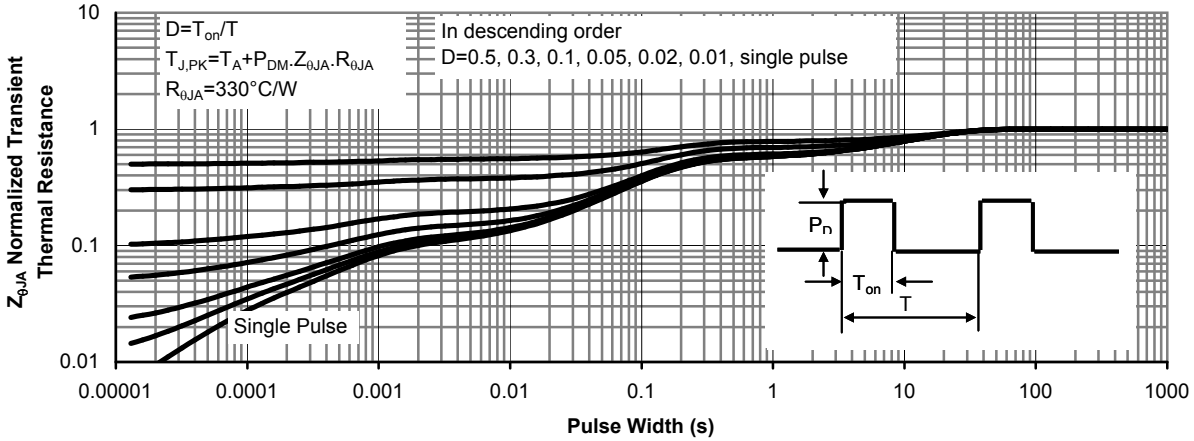
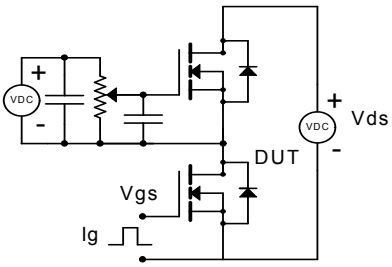
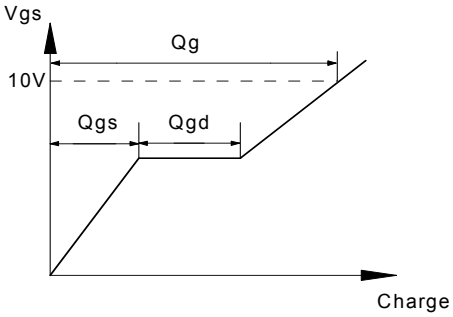


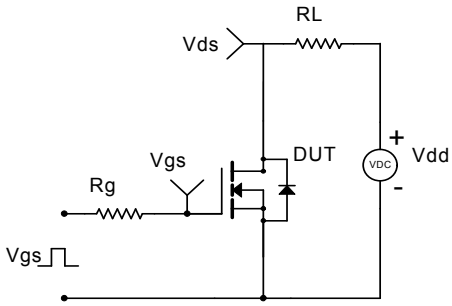
Figure 11: Normalized Maximum Transient Thermal Impedance

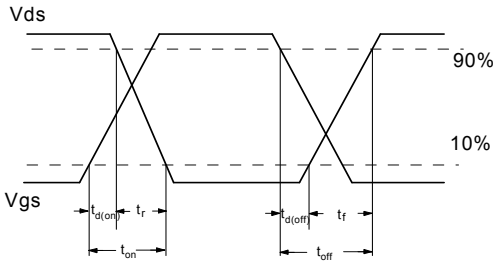
Gate Charge Test Circuit & Waveform



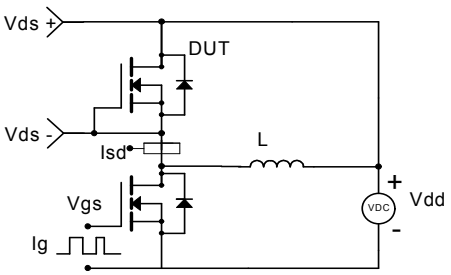


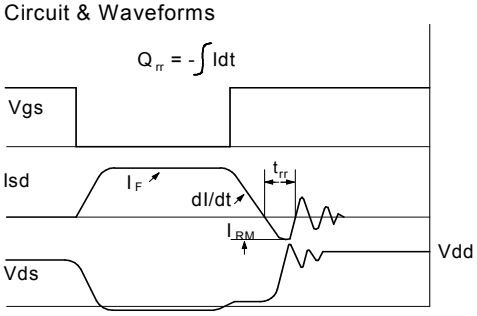
Resistive Switching Test Circuit & Waveforms



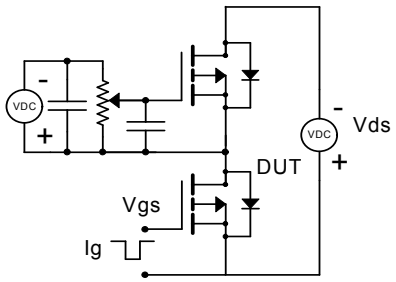


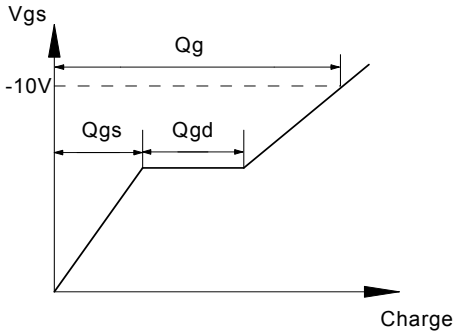
Diode Recovery Test Circuit & Waveforms



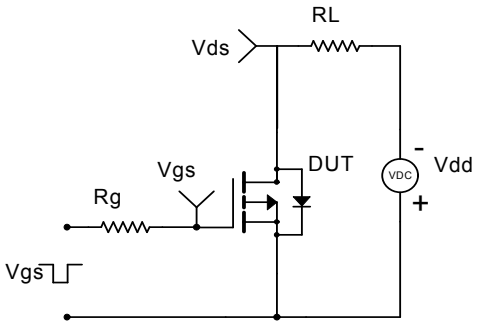


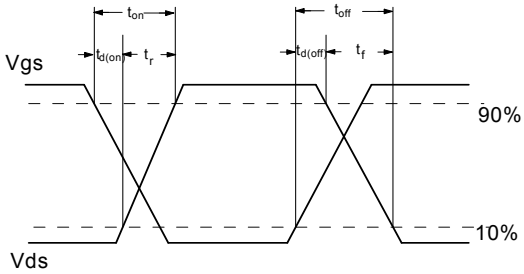
Gate Charge Test Circuit & Waveform





Resistive Switching Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms